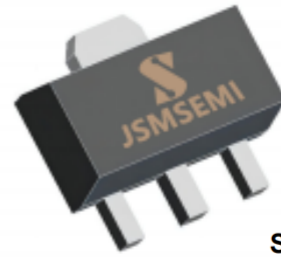


**FEATURES**

Compliment to PXT8050


**SOT-89**

- 1.BASE
- 2.COLLECTOR
- 3.EMITTER

**MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	-40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-25	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-1.5	A
P <sub>C</sub>	Collector Power Dissipation	0.5	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

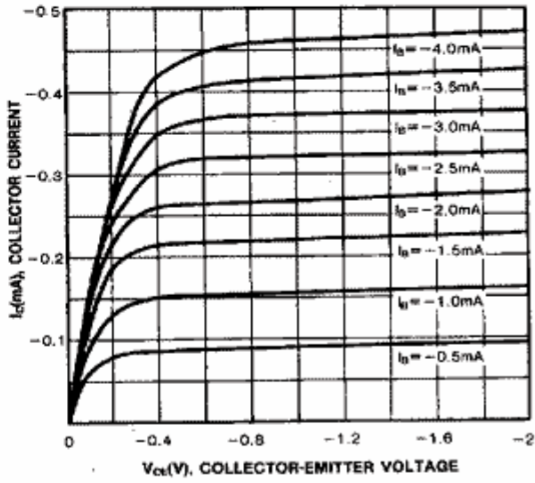
**ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -100μA, I <sub>E</sub> =0	-40		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -0.1mA, I <sub>B</sub> =0	-25		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -100μA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -40 V, I <sub>E</sub> =0		-0.1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> = -20V, I <sub>B</sub> =0		-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0		-0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA	85	400	
	h <sub>FE(2)</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -800mA	40		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-800mA, I <sub>B</sub> = -80mA		-0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-800mA, I <sub>B</sub> = -80mA		-1.2	V
Base-emitter on voltage	V <sub>BE(on)</sub>	I <sub>C</sub> =-1V, V <sub>CE</sub> =-10mA		-1	V
Base-emitter positive favor voltage	V <sub>BEF</sub>	I <sub>B</sub> =-1A		-1.55	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -10V, I <sub>C</sub> = -50mA	100		MHz
output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		20	pF

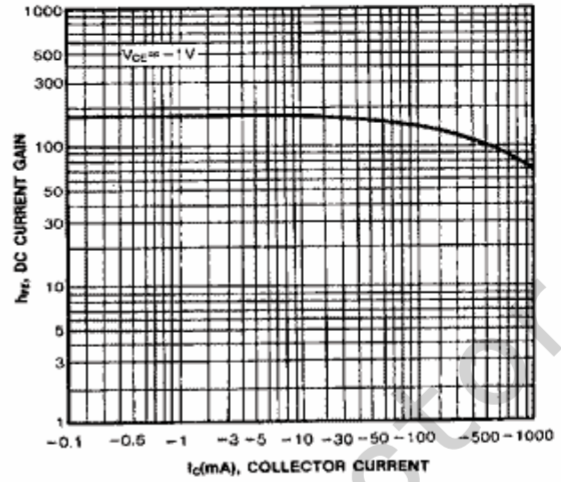
**CLASSIFICATION OF h<sub>FE(1)</sub>**

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

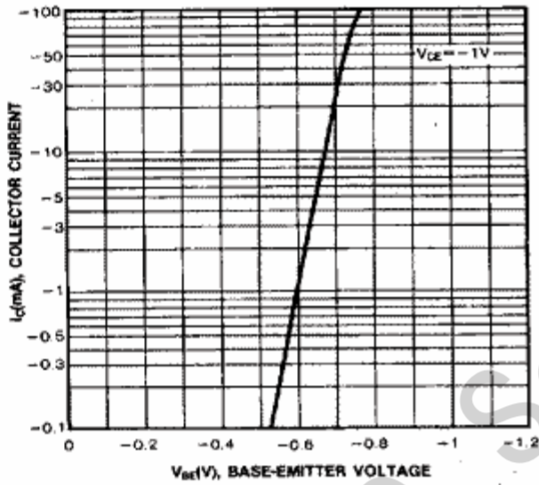
STATIC CHARACTERISTIC



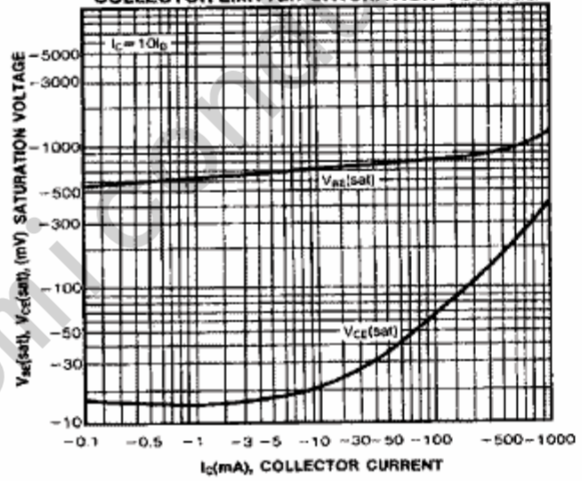
DC CURRENT GAIN



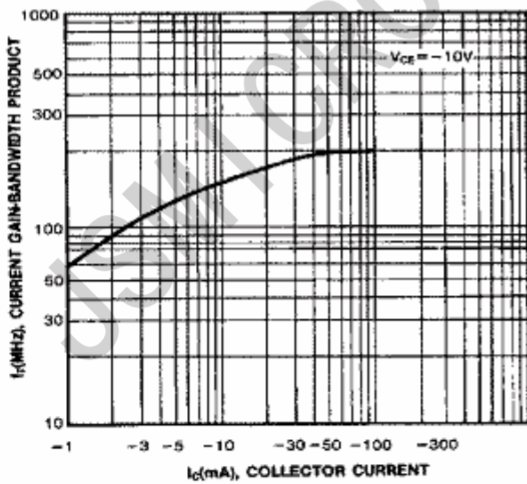
BASE-EMITTER ON VOLTAGE



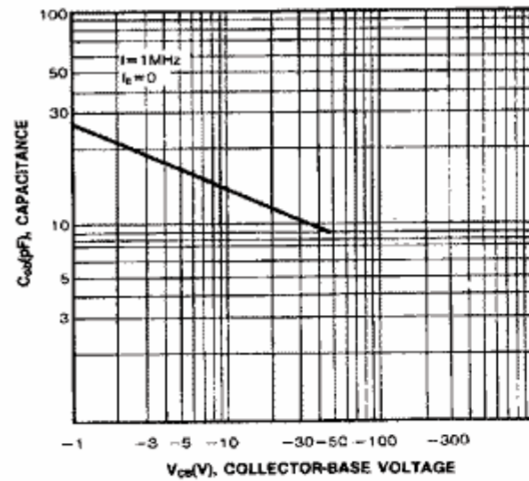
BASE-EMITTER SATURATION VOLTAGE  
COLLECTOR-EMITTER SATURATION VOLTAGE



CURRENT GAIN-BANDWIDTH PRODUCT

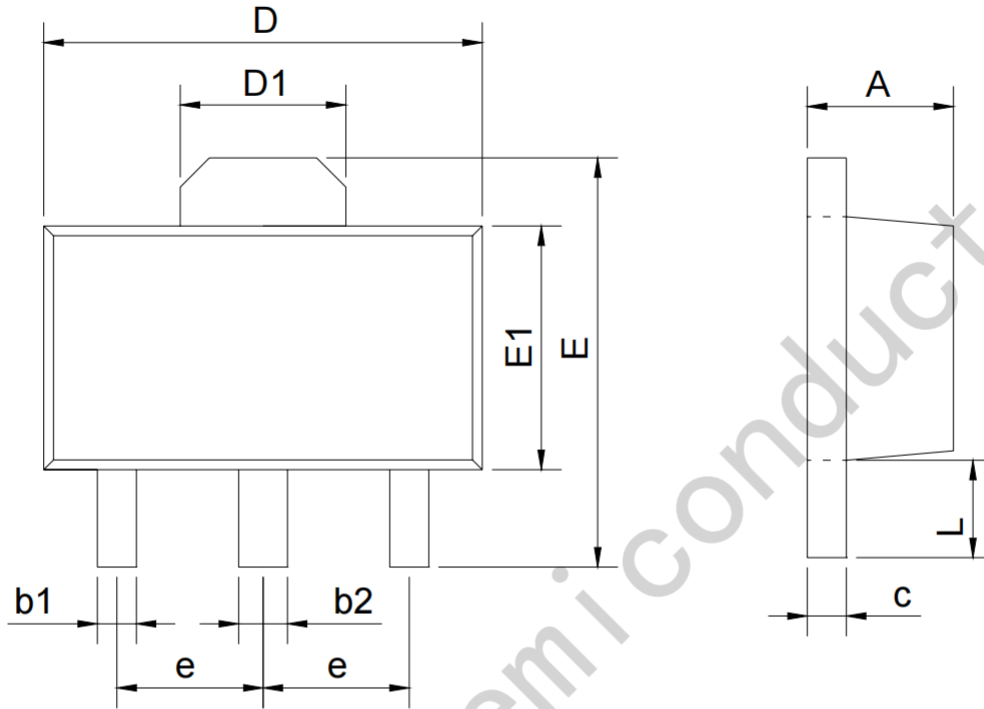


COLLECTOR OUTPUT CAPACITANCE



## Package Information

SOT-89



SYMBOL	mm	
	min	max
A	1.40	1.60
b1	0.35	0.50
b2	0.45	0.60
c	0.36	0.46
D	4.30	4.70
D1	1.40	1.80
E	4.00	4.40
E1	2.30	2.70
e	1.50BSC	
L	0.80	1.20

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